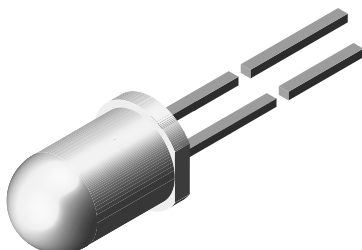


# High Speed Infrared Emitting Diode, 850 nm, GaAlAs Double Hetero



94 8389

## DESCRIPTION

TSHG6210 is an infrared, 850 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted plastic package.

## FEATURES

- Package type: leaded
- Package form: T-1 $\frac{3}{4}$
- Dimensions (in mm):  $\varnothing$  5
- Peak wavelength:  $\lambda_p = 850$  nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity:  $\varphi = \pm 10^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- High modulation bandwidth:  $f_c = 18$  MHz
- Good spectral matching with CMOS cameras
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

## APPLICATIONS

- Infrared radiation source for operation with CMOS cameras
- High speed IR data transmission
- Smoke-automatic fire detectors

## PRODUCT SUMMARY

COMPONENT	$I_e$ (mW/sr)	$\varphi$ (deg)	$\lambda_p$ (nm)	$t_r$ (ns)
TSHG6210	230	$\pm 10$	850	20

### Note

Test conditions see table "Basic Characteristics"

## ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSHG6210	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$

### Note

MOQ: minimum order quantity

## ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		$V_R$	5	V
Forward current		$I_F$	100	mA
Peak forward current	$t_p/T = 0.5$ , $t_p = 100$ $\mu$ s	$I_{FM}$	200	mA
Surge forward current	$t_p = 100$ $\mu$ s	$I_{FSM}$	1	A
Power dissipation		$P_V$	180	mW
Junction temperature		$T_j$	100	$^\circ$ C
Operating temperature range		$T_{amb}$	- 40 to + 85	$^\circ$ C
Storage temperature range		$T_{stg}$	- 40 to + 100	$^\circ$ C
Soldering temperature	$t \leq 5$ s, 2 mm from case	$T_{sd}$	260	$^\circ$ C
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	$R_{thJA}$	230	K/W

### Note

$T_{amb} = 25$   $^\circ$ C, unless otherwise specified

# Vishay Semiconductors High Speed Infrared Emitting Diode, 850 nm, GaAlAs Double Hetero

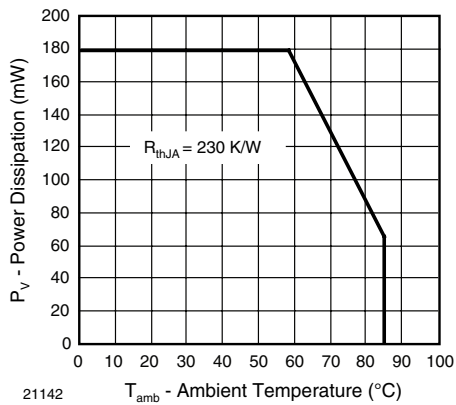


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

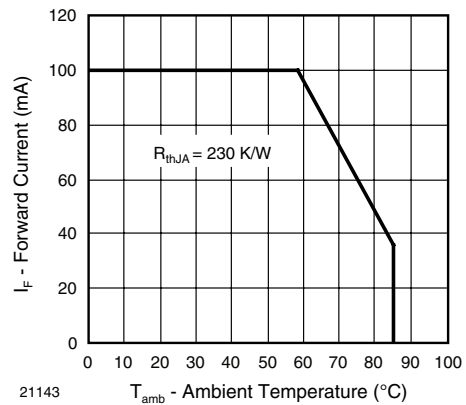


Fig. 2 - Forward Current Limit vs. Ambient Temperature

## BASIC CHARACTERISTICS

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100 \text{ mA}$ , $t_p = 20 \text{ ms}$	$V_F$		1.5	1.8	V
	$I_F = 1 \text{ A}$ , $t_p = 100 \mu\text{s}$	$V_F$		2.3		V
Temperature coefficient of $V_F$	$I_F = 1 \text{ mA}$	$TK_{VF}$		- 1.8		mV/K
Reverse current	$V_R = 5 \text{ V}$	$I_R$			10	$\mu\text{A}$
Junction capacitance	$V_R = 0 \text{ V}$ , $f = 1 \text{ MHz}$ , $E = 0$	$C_j$		125		pF
Radiant intensity	$I_F = 100 \text{ mA}$ , $t_p = 20 \text{ ms}$	$I_e$	140	230	420	mW/sr
	$I_F = 1 \text{ A}$ , $t_p = 100 \mu\text{s}$	$I_e$		2300		mW/sr
Radiant power	$I_F = 100 \text{ mA}$ , $t_p = 20 \text{ ms}$	$\phi_e$		55		mW
Temperature coefficient of $\phi_e$	$I_F = 100 \text{ mA}$	$TK_{\phi_e}$		- 0.35		%/K
Angle of half intensity		$\varphi$		$\pm 10$		deg
Peak wavelength	$I_F = 100 \text{ mA}$	$\lambda_p$	820	850	880	nm
Spectral bandwidth	$I_F = 100 \text{ mA}$	$\Delta\lambda$		40		nm
Temperature coefficient of $\lambda_p$	$I_F = 100 \text{ mA}$	$TK_{\lambda_p}$		0.25		nm/K
Rise time	$I_F = 100 \text{ mA}$	$t_r$		20		ns
Fall time	$I_F = 100 \text{ mA}$	$t_f$		13		ns
Cut-off frequency	$I_{DC} = 70 \text{ mA}$ , $I_{AC} = 30 \text{ mA pp}$	$f_c$		18		MHz
Virtual source diameter		$d$		3.7		mm

### Note

$T_{amb} = 25^\circ\text{C}$ , unless otherwise specified

# **BASIC CHARACTERISTICS**

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

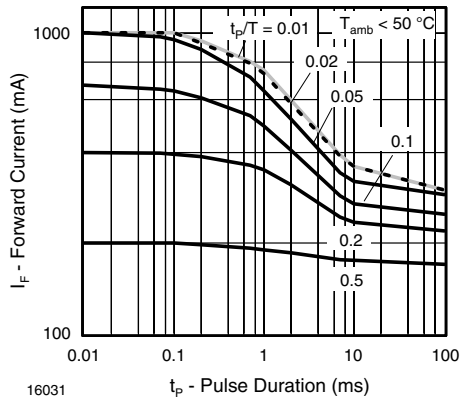


Fig. 3 - Pulse Forward Current vs. Pulse Duration

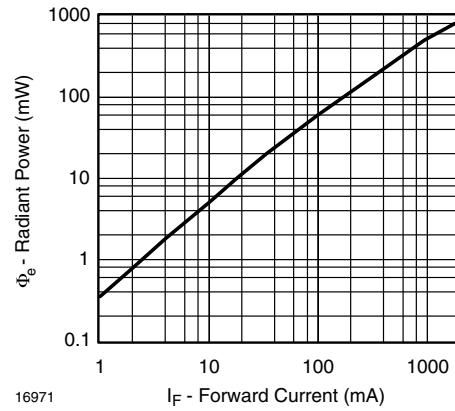


Fig. 6 - Radiant Power vs. Forward Current

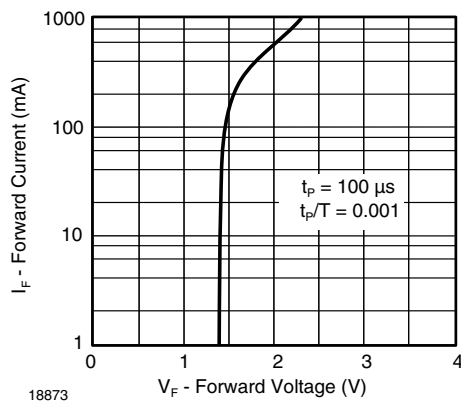


Fig. 4 - Forward Current vs. Forward Voltage

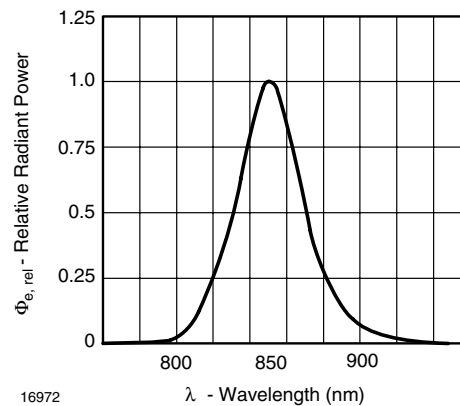


Fig. 7 - Relative Radiant Power vs. Wavelength

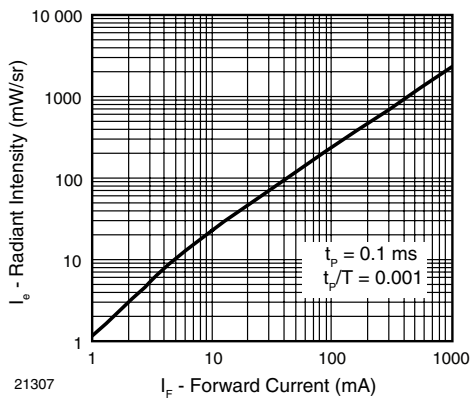


Fig. 5 - Radiant Intensity vs. Forward Current

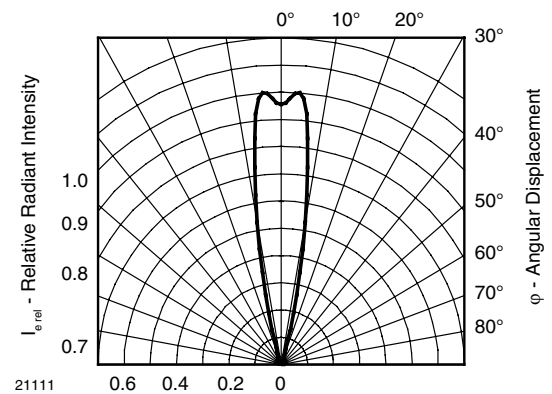
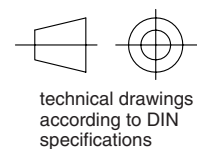


Fig. 8 - Relative Radiant Intensity vs. Angular Displacement

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